

Designer's™ Data Sheet
SWITCHMODE™ NPN Bipolar
Power Transistor for Electronic
Light Ballast and Switching
Power Supply Applications

The MJE/MJF18206 have an application specific state-of-the-art die dedicated to the electronic ballast ("light ballast") and power supply applications.

- Improved Global Efficiency Due to Low Base Drive Requirements:
 - High and Flat DC Current Gain h_{FE}
 - Fast Switching
 - No Coil Required in Base Circuit for fast Turn-Off (No Current Tail)
- Full Characterization at 125°C
- Motorola "6 SIGMA" Philosophy Provides Tight and Reproducible Parametric Distributions
- Two Package Choices: Standard TO-220 or Isolated TO-220

MAXIMUM RATINGS

Rating	Symbol	MJE18206	MJF18206	Unit
Collector-Emitter Voltage	V_{CEO}	600		Vdc
Collector-Base Voltage	V_{CBO}	1200		Vdc
Collector-Emitter Voltage	V_{CES}	1200		Vdc
Emitter-Base Voltage	V_{EBO}	10		Vdc
Collector Current — Continuous	I_C	8		Adc
— Peak (1)	I_{CM}	16		
Base Current — Continuous	I_B	5		Adc
— Peak (1)	I_{BM}	9		
RMS Isolation Voltage (2) (for 1 sec, R.H. ≤ 30%) $T_C = 25^\circ\text{C}$	Per Figure 22 Per Figure 23 Per Figure 24 V_{ISOL1} V_{ISOL2} V_{ISOL3}		4500 3500 1500	Volts
*Total Device Dissipation @ $T_C = 25^\circ\text{C}$ *Derate above 25°C	P_D	100 0.8	40 0.32	Watt W/°C
Operating and Storage Temperature	T_J, T_{stg}	-65 to 150		°C

THERMAL CHARACTERISTICS

Rating	Symbol	MJE18206	MJF18206	Unit
Thermal Resistance — Junction to Case	$R_{\theta JC}$	1.25	3.125	°C/W
— Junction to Ambient	$R_{\theta JA}$	62.5	62.5	
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	T_L	260		°C

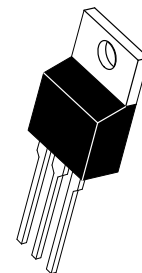
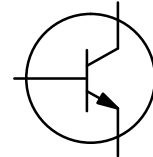
- (1) Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.
(2) Proper strike and creepage distance must be provided.

Designer's Data for "Worst Case" Conditions — The Designer's Data Sheet permits the design of most circuits entirely from the information presented. SOA Limit curves — representing boundaries on device characteristics — are given to facilitate "worst case" design.

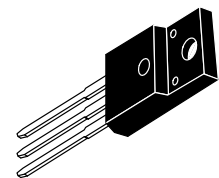
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MJE18206
MJF18206

POWER TRANSISTORS
8 AMPERES
1200 VOLTS
40 and 100 WATTS



CASE 221A-06
TO-220AB



CASE 221D-02
TO-220 FULLPACK

MJE18206 MJF18206

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $L = 25\text{ mH}$) ($I_C = 200\text{ mA}$, $L = 25\text{ mH}$, $R = 200\ \Omega$)	$V_{CEO(sus)}$ $V_{CER(sus)}$	550 600	630 700		Vdc
Collector–Base Breakdown Voltage ($I_{CBO} = 1\text{ mA}$, $I_E = 0$)	V_{CBO}	1200	1320		Vdc
Emitter–Base Breakdown Voltage ($I_{EBO} = 1\text{ mA}$, $I_C = 0$)	V_{EBO}	10	12.9		Vdc
Collector Cutoff Current ($V_{CE} = 550\text{ V}$, $I_B = 0$) ($V_{CE} = 550\text{ V}$, $I_B = 0$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ I_{CEO}			200 2000	μAdc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CES}$, $V_{BE} = 0$) ($V_{CE} = 1000\text{ V}$, $V_{BE} = 0$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ I_{CES}			100 1000 100	μAdc
Collector Cutoff Current ($V_{CB} = 1200\text{ V}$, $I_E = 0$)	I_{CBO}			100	μAdc
Emitter–Cutoff Current ($V_{EB} = 9\text{ Vdc}$, $I_C = 0$)	I_{EBO}			100	μAdc

ON CHARACTERISTICS

Base–Emitter Saturation Voltage ($I_C = 1.3\text{ Adc}$, $I_B = 0.13\text{ Adc}$) ($I_C = 2\text{ Adc}$, $I_B = 0.4\text{ Adc}$) ($I_C = 3\text{ Adc}$, $I_B = 0.6\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{BE(sat)}$		0.77 0.67 0.85 0.75 0.91 0.8	1 0.9 1.1 1 1.1 1	Vdc
Collector–Emitter Saturation Voltage ($I_C = 1.3\text{ Adc}$, $I_B = 0.13\text{ Adc}$) ($I_C = 3\text{ Adc}$, $I_B = 0.6\text{ Adc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	$V_{CE(sat)}$		0.3 0.4 0.4 0.8	0.75 1 0.75 1.25	Vdc
DC Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 1\text{ Adc}$, $V_{CE} = 5\text{ Vdc}$) ($I_C = 3\text{ Adc}$, $V_{CE} = 1\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 5\text{ Vdc}$)	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	h_{FE}	18 18 5 4 11	25 25 20 8 6 33	— 45 — 50	—

DYNAMIC CHARACTERISTICS

Current Gain Bandwidth ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1\text{ MHz}$)	f_T		13		MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1\text{ MHz}$)	C_{ob}			200	pF
Input Capacitance ($V_{EB} = 8\text{ Vdc}$)	C_{ib}			2000	pF

DYNAMIC SATURATION VOLTAGE

Dynamic Saturation Voltage: Determined 1 μs and 3 μs respectively after rising I_{B1} reaches 90% of final I_{B1}	$I_C = 1.3\text{ Adc}$ $I_{B1} = 130\text{ mAdc}$ $V_{CC} = 300\text{ V}$	@ 1 μs	@ $T_C = 25^\circ\text{C}$	$V_{CE(dsat)}$	7.5	V
		@ 3 μs	@ $T_C = 25^\circ\text{C}$		4.5	
	$I_C = 3\text{ Adc}$ $I_{B1} = 0.6\text{ Adc}$ $V_{CC} = 300\text{ V}$	@ 1 μs	@ $T_C = 25^\circ\text{C}$		14.5	
		@ 3 μs	@ $T_C = 25^\circ\text{C}$		6	

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit		
SWITCHING CHARACTERISTICS: Resistive Load (D.C. $\leq 10\%$, Pulse Width = 40 μs)								
Turn-on Time	$I_C = 3 \text{ Adc}$, $I_{B1} = 0.6 \text{ Adc}$ $I_{B2} = 1.5 \text{ Adc}$ $V_{CC} = 300 \text{ Vdc}$	@ $T_C = 25^\circ\text{C}$	t_{on}		200	350	ns	
Turn-off Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{off}		2 2.5	2.5	μs	
Turn-on Time	$I_C = 3 \text{ Adc}$, $I_{B1} = 0.6 \text{ Adc}$ $I_{B2} = 0.6 \text{ Adc}$ $V_{CC} = 300 \text{ Vdc}$	@ $T_C = 25^\circ\text{C}$	t_{on}		190	250	ns	
Turn-off Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{off}		3.7 4.5	4.5	μs	
Turn-on Time	$I_C = 1 \text{ Adc}$, $I_{B1} = 70 \text{ mAdc}$ $I_{B2} = 1 \text{ Adc}$ $V_{CC} = 125 \text{ Vdc}$ PW = 70 μs	@ $T_C = 25^\circ\text{C}$	t_d		125	300	ns	
				t_r		400	750	ns
Turn-off Time		@ $T_C = 25^\circ\text{C}$	t_s		600	1.2	μs	
				t_f		450	700	ns
Turn-on Time	$I_C = 1 \text{ Adc}$, $I_{B1} = 100 \text{ mAdc}$ $I_{B2} = 500 \text{ mAdc}$ $V_{CC} = 300 \text{ Vdc}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{on}		250 225	350	ns	
Turn-off Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_{off}		2 2.5	2.75	μs	

SWITCHING CHARACTERISTICS: Inductive Load ($V_{clamp} = 300 \text{ V}$, $V_{CC} = 15 \text{ V}$, $L = 200 \mu\text{H}$)

Fall Time	$I_C = 1.3 \text{ Adc}$ $I_{B1} = 0.13 \text{ Adc}$ $I_{B2} = 0.65 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f		150 225	200	ns
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s		1.6 1.9	2	μs
Crossover Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_c		260 300	350	ns
Fall Time	$I_C = 3 \text{ Adc}$ $I_{B1} = 0.6 \text{ Adc}$ $I_{B2} = 1.5 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f		300 400	450	ns
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s		2.25 2.5	2.75	μs
Crossover Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_c		500 700	800	ns
Fall Time	$I_C = 3 \text{ Adc}$ $I_{B1} = 0.6 \text{ Adc}$ $I_{B2} = 0.6 \text{ Adc}$	@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_f		350 500	500	ns
Storage Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_s		4.25 5.1	5	μs
Crossover Time		@ $T_C = 25^\circ\text{C}$ @ $T_C = 125^\circ\text{C}$	t_c		600 1100	800	ns

TYPICAL STATIC CHARACTERISTICS

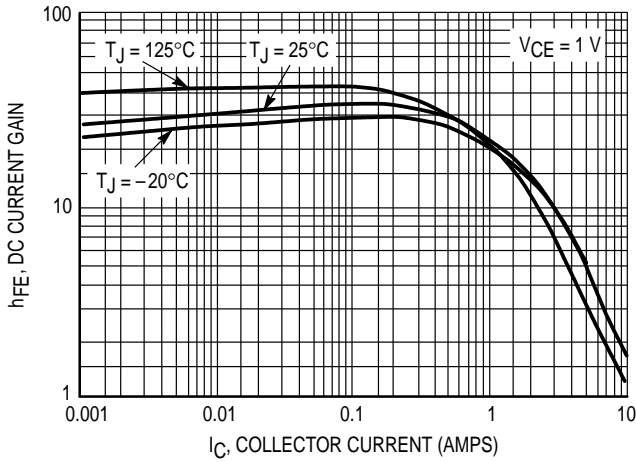


Figure 1. DC Current Gain @ 1 Volt

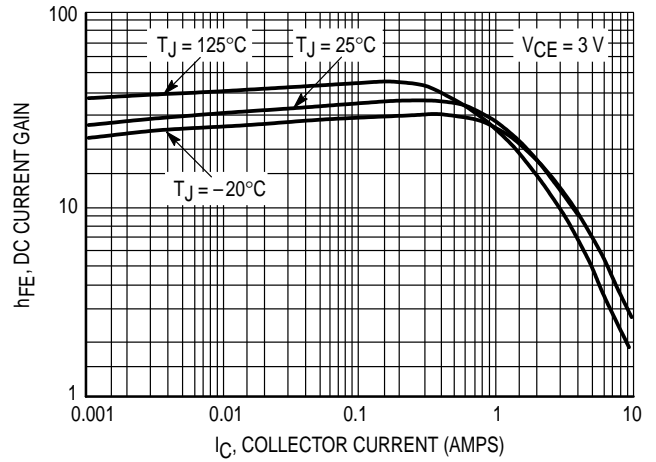


Figure 2. DC Current Gain @ 3 Volts

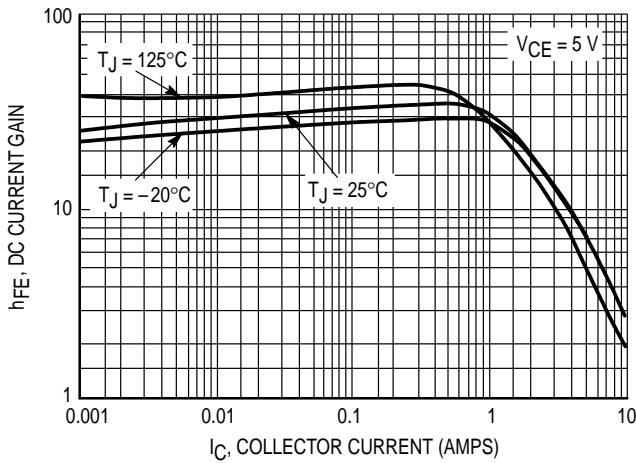


Figure 3. DC Current Gain @ 5 Volts

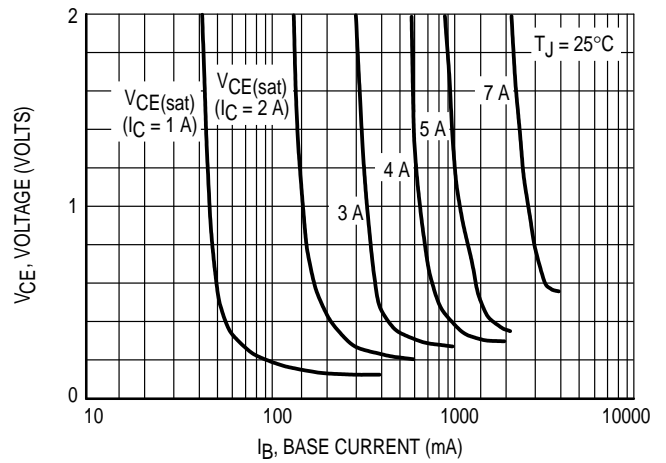


Figure 4. Collector Saturation Region

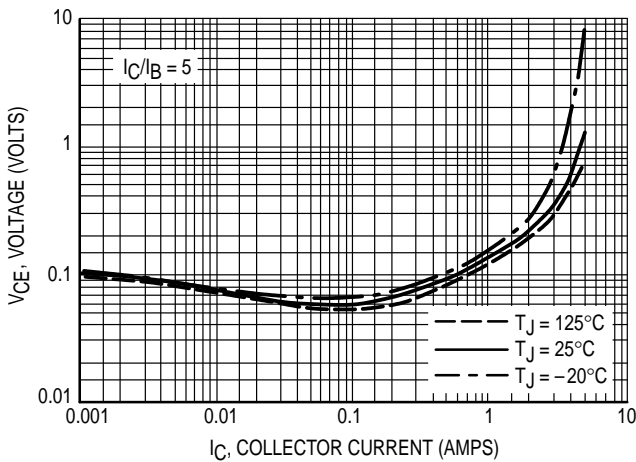


Figure 5A. Collector-Emmitter Saturation Voltage

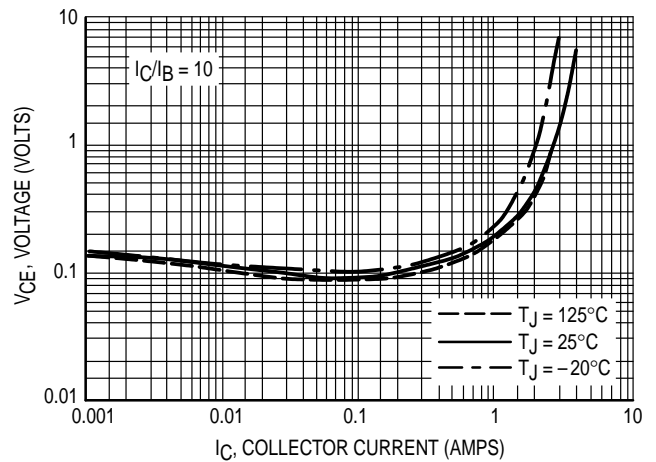


Figure 5B. Collector-Emmitter Saturation Voltage

TYPICAL STATIC CHARACTERISTICS

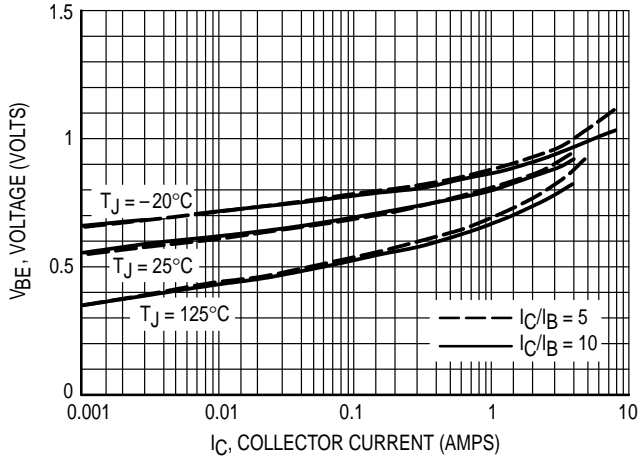


Figure 6. Base-Emitter Saturation Region

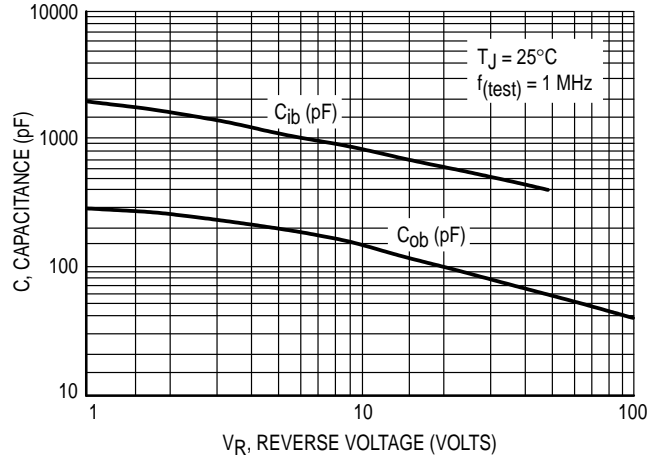


Figure 7. Capacitance

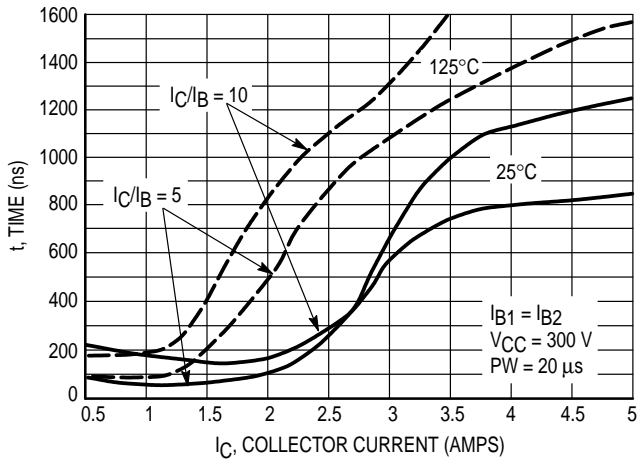


Figure 8. Resistive Switching, t_{on}

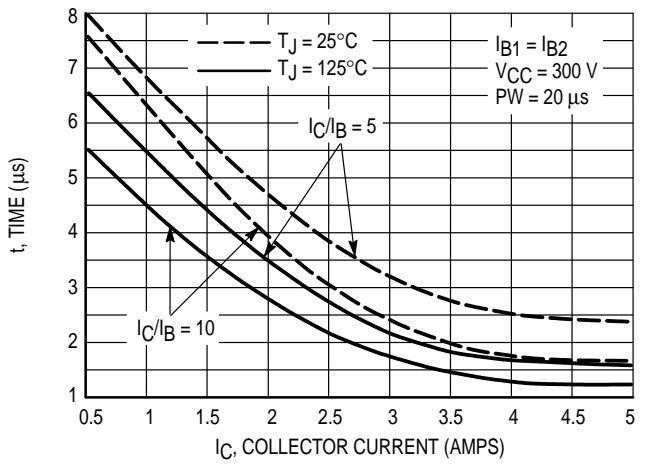


Figure 9. Resistive Switching, t_{off}

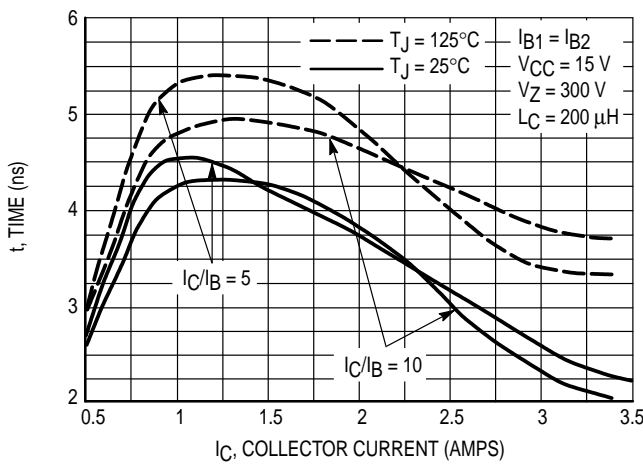


Figure 10. Inductive Storage Time, t_{si}

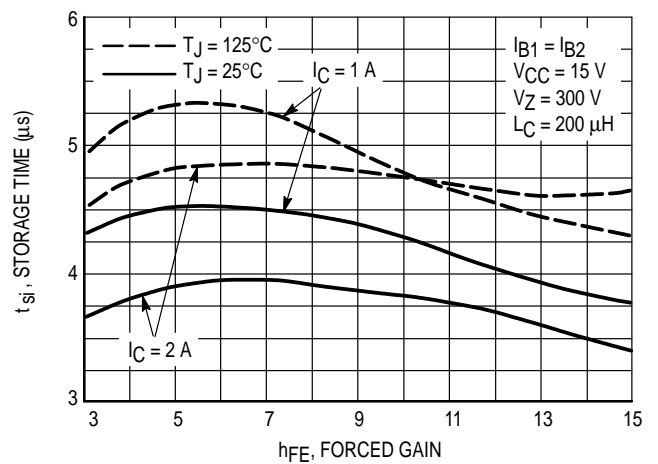


Figure 11. Inductive Storage Time

TYPICAL STATIC CHARACTERISTICS

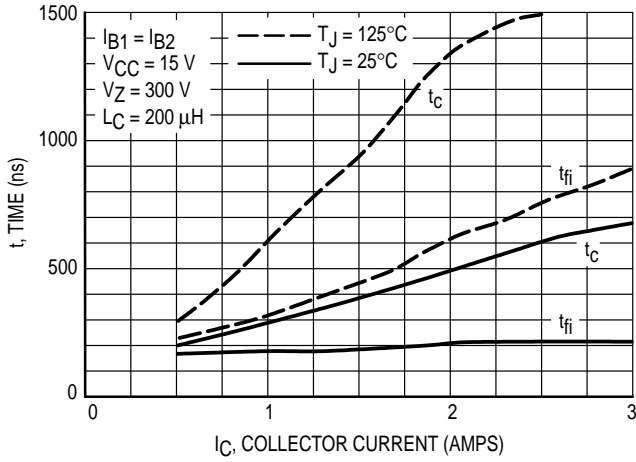


Figure 12. Inductive Switching, t_c & t_{fi} @ $I_C/I_B = 5$

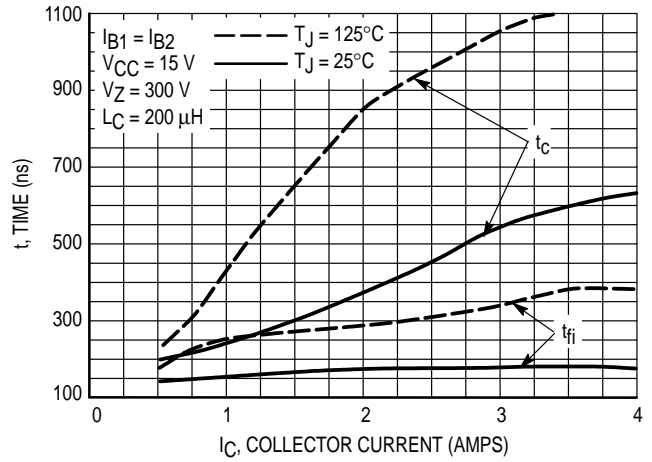


Figure 13. Inductive Switching, t_c & t_{fi} @ $I_C/I_B = 10$

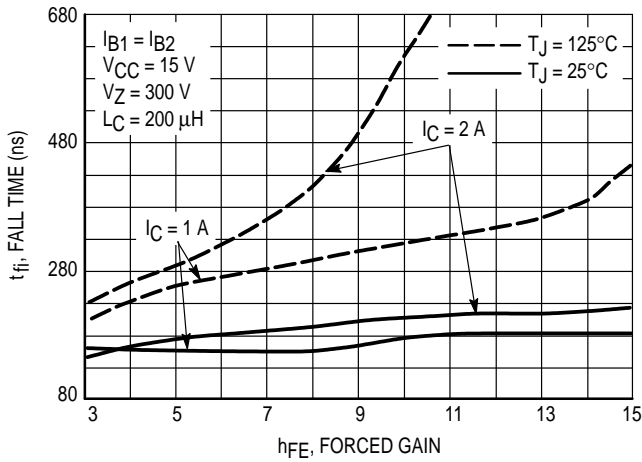


Figure 14. Inductive Fall Time

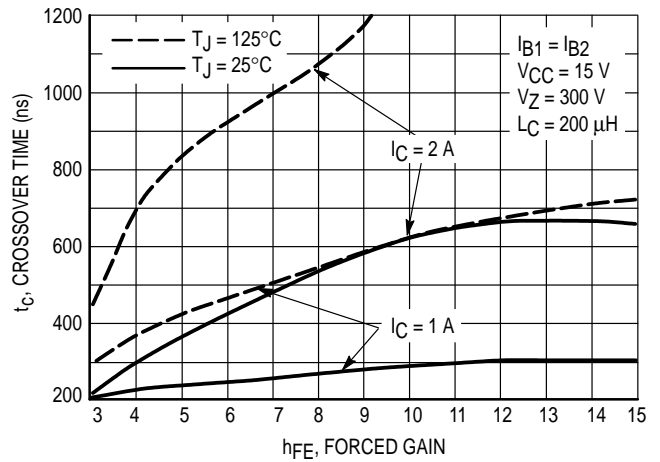


Figure 15. Inductive Crossover Time

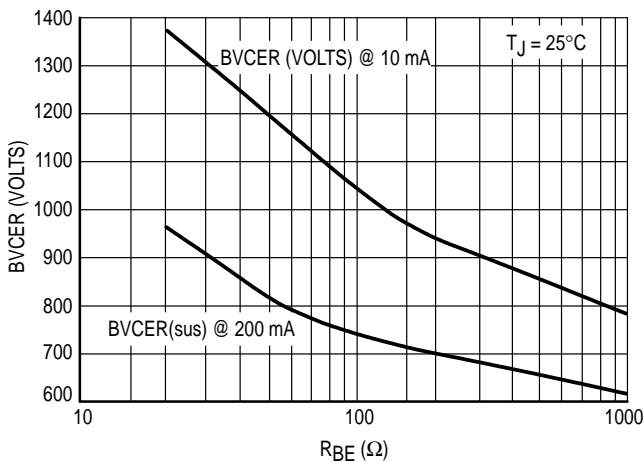


Figure 16. $BV_{CEr} = f(R_{BE})$

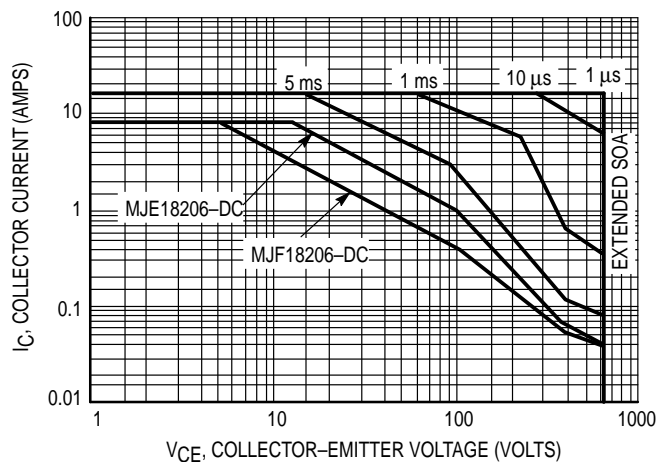


Figure 17. Forward Bias Safe Operating Area

TYPICAL STATIC CHARACTERISTICS

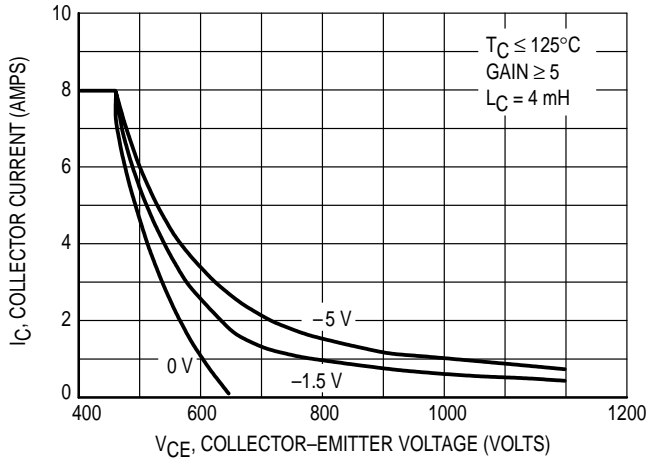


Figure 18. Reverse Bias Switching Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figure 17 is based on $T_C = 25^\circ\text{C}$; $T_J(\text{pk})$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C > 25^\circ\text{C}$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 17 may be found at any case temperature by using

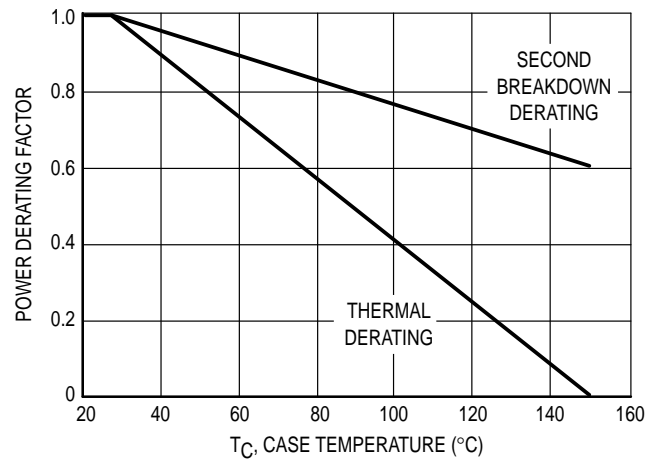


Figure 19. Forward Bias Power Derating

the appropriate curve on Figure 19.

$T_J(\text{pk})$ may be calculated from the data in Figures 22 and 23. At any case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown. For inductive loads, high voltage and current must be sustained simultaneously during turn-off with the base-to-emitter junction reverse biased. The safe level is specified as a reverse-biased safe operating area (Figure 18). This rating is verified under clamped conditions so that the device is never subjected to an avalanche mode.

TYPICAL SWITCHING CHARACTERISTICS
($I_{B1} = I_{B2}$ FOR ALL CURVES)

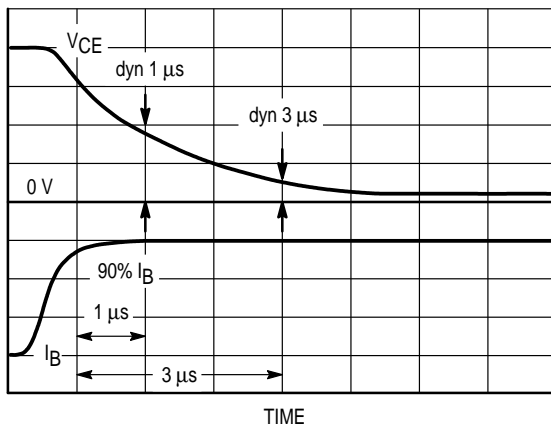


Figure 20. Dynamic Saturation Voltage Measurements

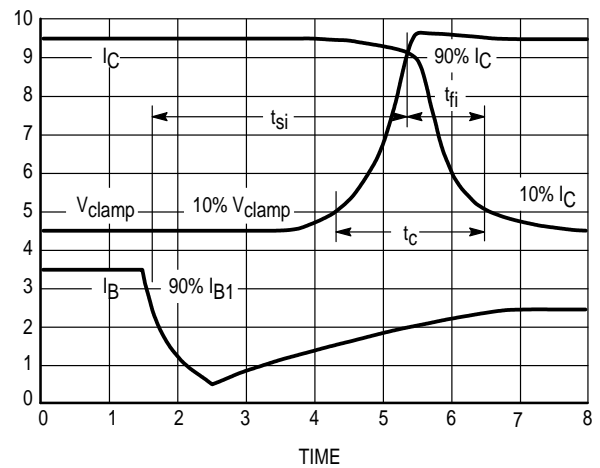
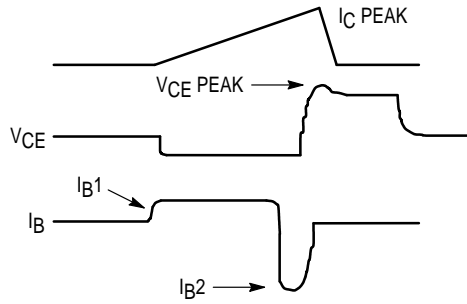
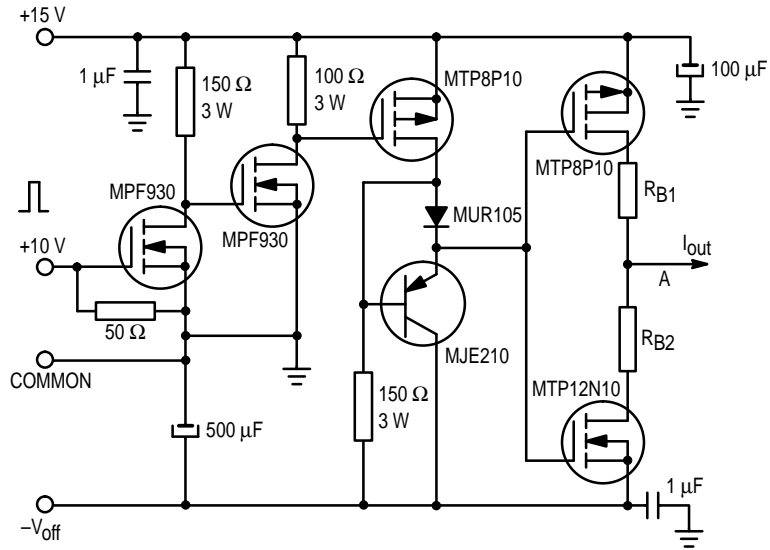


Figure 21. Inductive Switching Measurements

TYPICAL SWITCHING CHARACTERISTICS
($I_{B1} = I_{B2}$ FOR ALL CURVES)

Table 1. Inductive Load Switching Drive Circuit



$V_{(BR)CEO(sus)}$
 $L = 10 \text{ mH}$
 $R_{B2} = \infty$
 $V_{CC} = 20 \text{ Volts}$
 $I_{C(pk)} = 100 \text{ mA}$

Inductive Switching
 $L = 200 \mu\text{H}$
 $R_{B2} = 0$
 $V_{CC} = 15 \text{ Volts}$
 R_{B1} selected for desired I_{B1}

RBSOA
 $L = 500 \mu\text{H}$
 $R_{B2} = 0$
 $V_{CC} = 15 \text{ Volts}$
 R_{B1} selected for desired I_{B1}

TYPICAL THERMAL RESPONSE
($I_{B1} = I_{B2}$ FOR ALL CURVES)

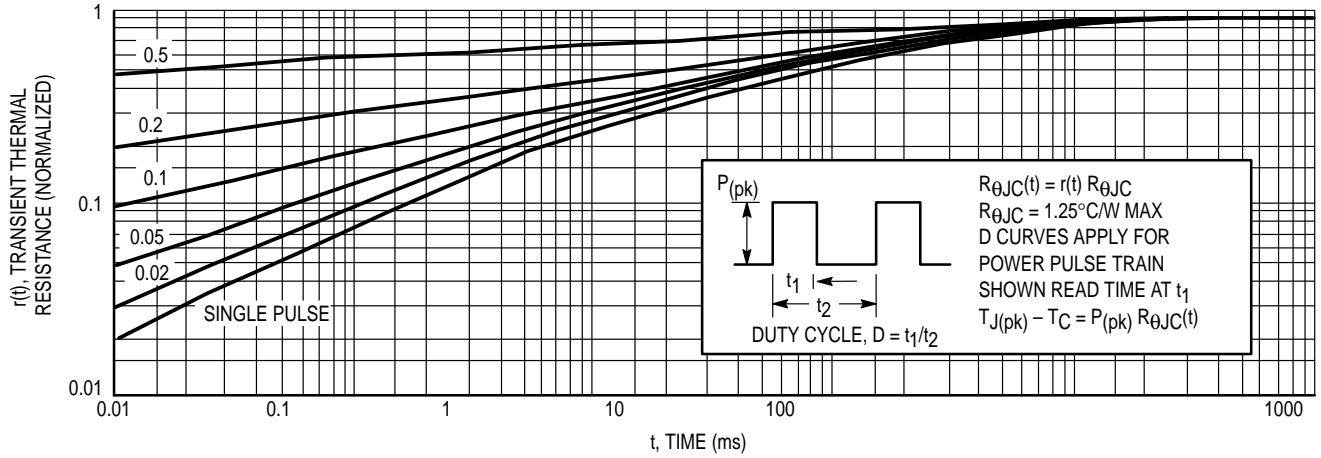


Figure 22. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJE18206

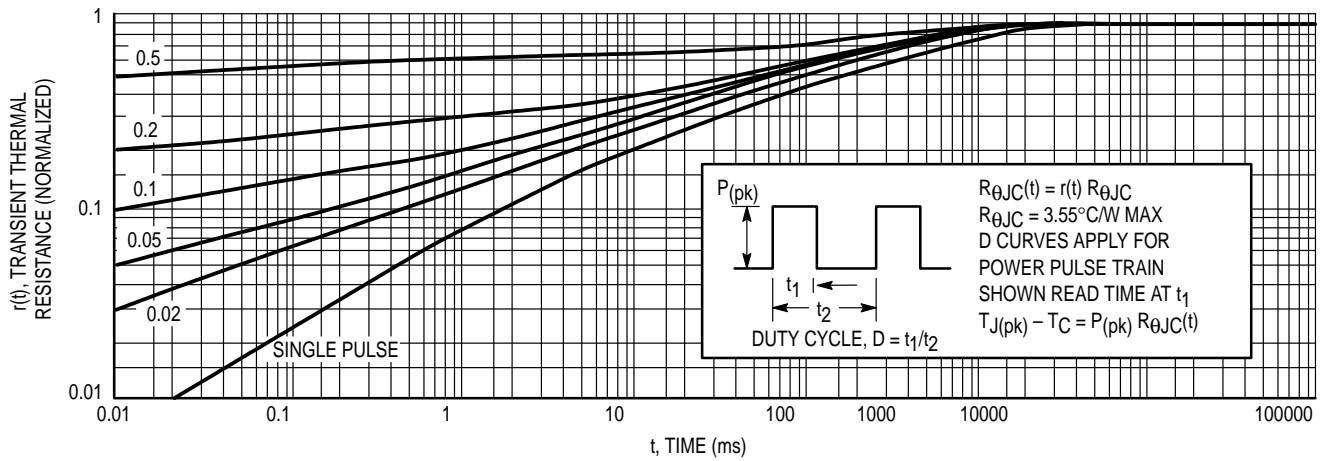
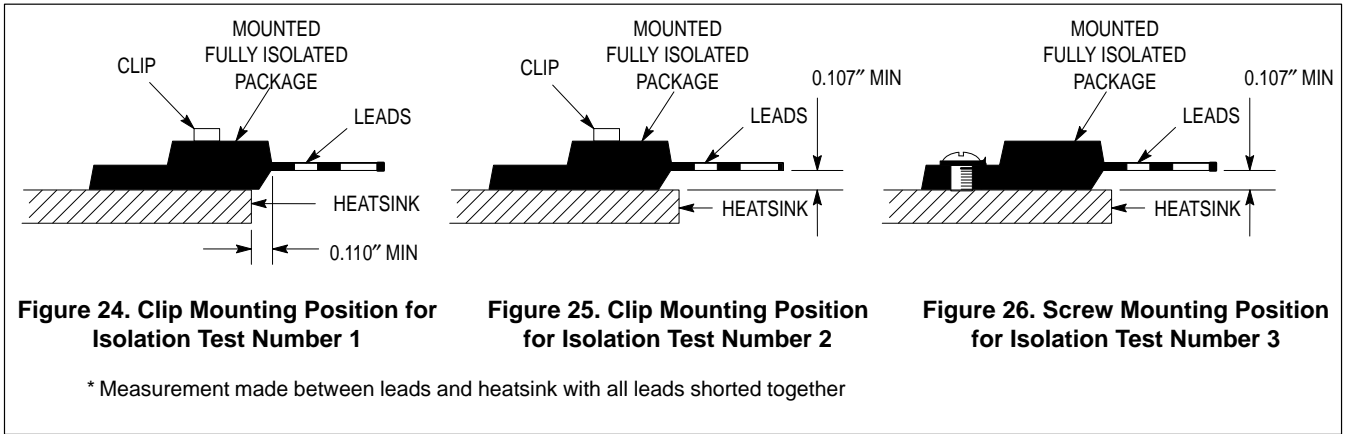
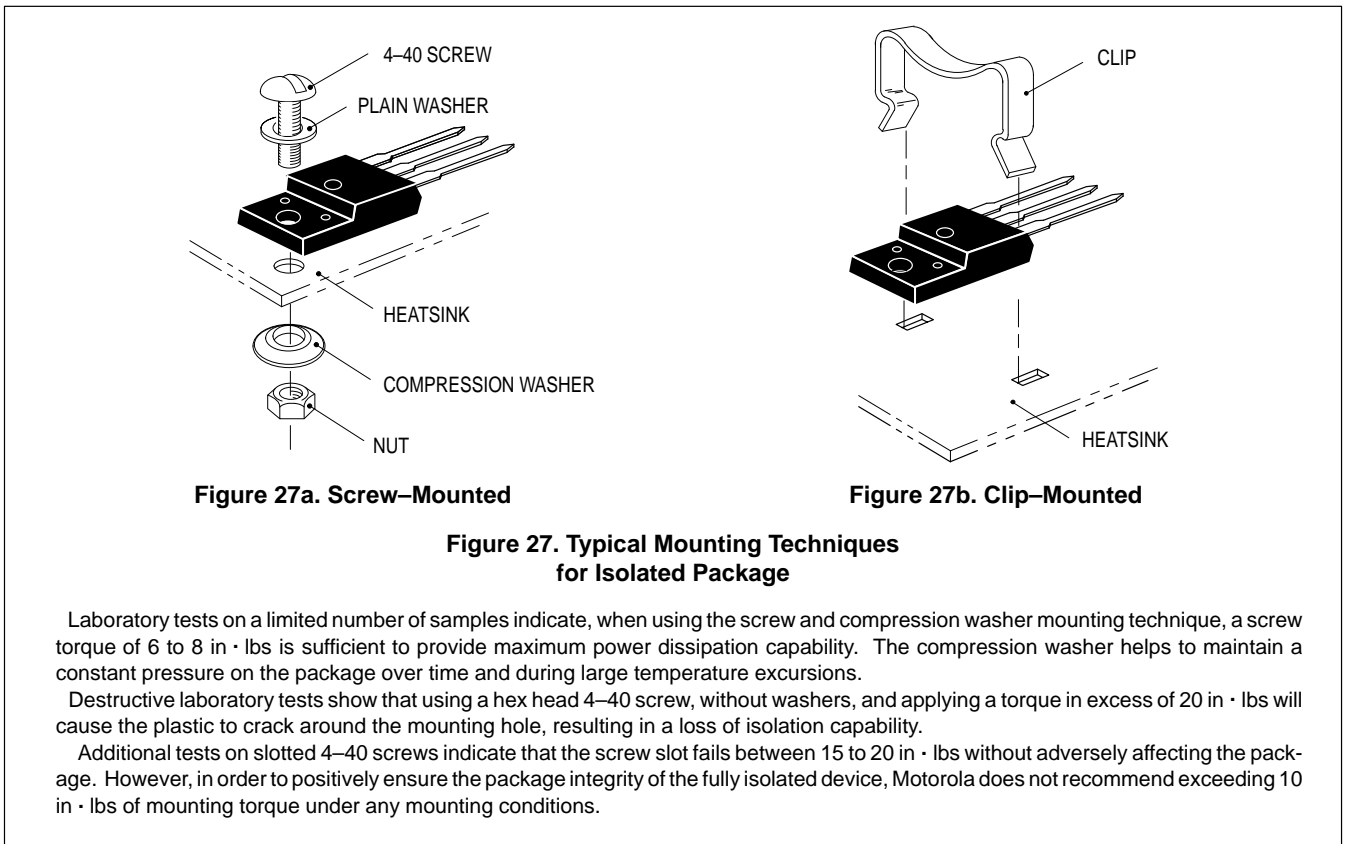


Figure 23. Typical Thermal Response ($Z_{\theta JC}(t)$) for MJF18206

TEST CONDITIONS FOR ISOLATION TESTS*

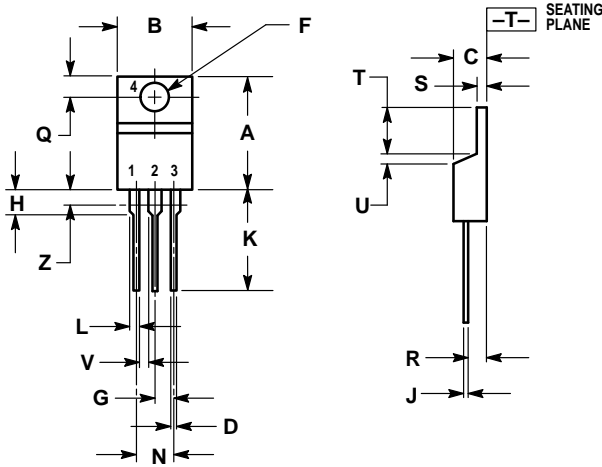


MOUNTING INFORMATION**



** For more information about mounting power semiconductors see Application Note AN1040.

PACKAGE DIMENSIONS

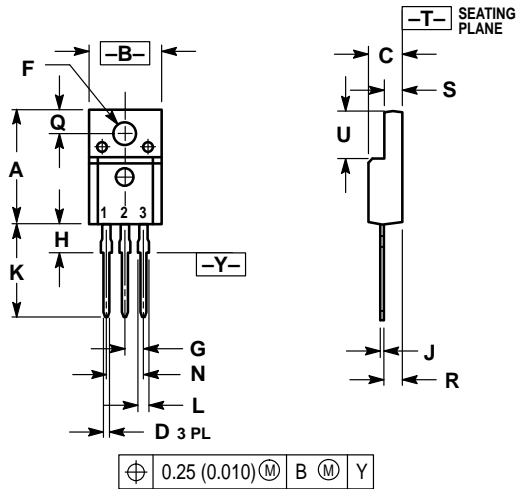


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

- STYLE 1:
 PIN 1. BASE
 2. COLLECTOR
 3. EMITTER
 4. COLLECTOR

CASE 221A-06
 TO-220AB
 ISSUE Y




- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.621	0.629	15.78	15.97
B	0.394	0.402	10.01	10.21
C	0.181	0.189	4.60	4.80
D	0.026	0.034	0.67	0.86
F	0.121	0.129	3.08	3.27
G	0.100 BSC	—	2.54 BSC	—
H	0.123	0.129	3.13	3.27
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
N	0.200 BSC	—	5.08 BSC	—
Q	0.126	0.134	3.21	3.40
R	0.107	0.111	2.72	2.81
S	0.096	0.104	2.44	2.64
U	0.259	0.267	6.58	6.78

- STYLE 1:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE

CASE 221D-02
 (ISOLATED TO-220 TYPE)
 UL RECOGNIZED: FILE #E69369
 ISSUE D

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